

CLAIMS

1. A method of operating a memory, comprising:
programming a particular portion of a data state to a memory cell, with a data randomizer in a first operating mode at a time of programming the particular portion of the data state to the memory cell; and
programming a remaining portion of the data state to the memory cell, with the data randomizer in a second operating mode different than the first operating mode at a time of programming the remaining portion of the data state to the memory cell.
2. The method of claim 1, wherein programming the particular portion of the data state comprises programming a particular digit position of the data state.
3. The method of claim 2, wherein programming the remaining portion of the data state comprises programming a different digit position of the data state.
4. The method of claim 3, wherein programming the different digit position of the data state further comprises programming each digit position of the data state other than the particular digit position.
5. The method of claim 1, wherein programming the particular portion of the data state to the memory cell, with the data randomizer in the first operating mode at the time of programming the particular portion of the data state to the memory cell, comprises programming the particular portion of the data state to the memory cell, with the data randomizer enabled at the time of programming the particular portion of the data state to the memory cell.
6. The method of claim 1, wherein programming the remaining portion of the data state, with the data randomizer in the second operating mode at the time of programming the remaining portion of the data state to the memory cell, comprises programming the

remaining portion of the data state, with the data randomizer disabled at the time of programming the remaining portion of the data state to the memory cell.

7. A method of operating a memory, comprising:
programming a particular digit position of a data state to a memory cell, with a data randomizer enabled at a time of programming the particular digit position of the data state to the memory cell; and
programming a different digit position of the data state to the memory cell, with the data randomizer disabled at a time of programming the different digit position of the data state to the memory cell.
8. The method of claim 7, wherein programming the particular digit position of the data state comprises programming a least significant bit of the data state.
9. The method of claim 8, wherein programming the least significant bit of the data state comprises programming the least significant bit of the data state using user data.
10. The method of claim 8, wherein programming the different digit position of the data state comprises programming a most significant bit of the data state.
11. The method of claim 10, wherein programming the most significant bit of the data state comprises programming the most significant bit of the data state using uniform data having a particular value.
12. The method of claim 11, wherein the data state is a particular data state of a plurality of data states to which the memory cell may be programmed, where each data state of the plurality of data states corresponds a respective threshold voltage range, and wherein programming the particular digit position of the data state to the memory cell, with the data randomizer enabled at the time of programming the particular digit position of the data state to the memory cell, and programming the different digit position of the data state to the memory cell, with the data randomizer disabled at the time of programming

the different digit position of the data state to the memory cell, programs the memory cell to a threshold voltage within either a lowest threshold voltage range of the plurality of data states or a highest threshold voltage range of the plurality of data states.

13. The method of claim 10, further comprising programming one or more additional digit positions of the data state.
14. A method of operating a memory, comprising:
for one or more first digit positions of a data state, programming the one or more first digit positions of the data state to a memory cell, with a data randomizer in a first operating mode at a time of programming the one or more first digit positions of the data state to the memory cell;
for one or more second digit positions of the data state, after programming the one or more first digit positions of the data state to the memory cell, with the data randomizer in the first operating mode at the time of programming the one or more first digit positions of the data state to the memory cell, programming the one or more second digit positions of the data state to the memory cell, with the data randomizer in a second operating mode different than the first operating mode at a time of programming the one or more second digit positions of the data state to the memory cell.
15. The method of claim 14, further comprising:
for one or more third digit positions of the data state, after programming the one or more second digit positions of the data state to the memory cell, with the data randomizer in the second operating mode at the time of programming the one or more second digit positions of the data state to the memory cell, programming the one or more third digit positions of the data state to the memory cell, with the data randomizer in the first operating mode at a time of programming the one or more third digit positions of the data state to the memory cell.

16. The method of claim 14, wherein programming the one or more first digit positions of the data state to the memory cell comprises programming only a single digit position of the data state to the memory cell, and wherein programming the one or more second digit positions of the data state to the memory cell comprises programming all remaining digit positions of the data state to the memory cell.
17. The method of claim 16, wherein programming only the single digit position of the data state to the memory cell comprises programming user data for the single digit position of the data state to the memory cell, and wherein programming all remaining digit positions of the data state to the memory cell comprises programming respective uniform data for each digit position of all remaining digit positions to the memory cell.
18. The method of claim 17, wherein the first operating mode of the data randomizer is an enabled operating mode and wherein the second operating mode of the data randomizer is a disabled operating mode.
19. The method of claim 14, wherein programming the one or more first digit positions of the data state to the memory cell comprises programming the one or more first digit positions of the data state to the memory cell as part of lower page data for a page of memory cells.
20. The method of claim 19, wherein programming the one or more second digit positions of the data state to the memory cell comprises programming the one or more second digit positions of the data state to the memory cell as part of upper page data for the page of memory cells.